



《风光欣》技术资料

STD123S

NPN SILICON TRANSISTOR

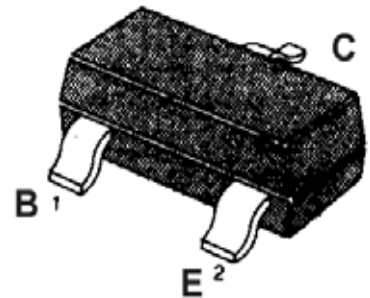
Features

- Low saturation medium current application
- Extremely low collector saturation voltage
- Suitable for low voltage large current drivers
- High DC current gain and large current capability

ABSOLUTE MAXIMUM RATINGS($T_A=25$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	30	V
Collector-Emitter Voltage	V_{CEO}	15	V
Emitter -Base Voltage	V_{EBO}	6.5	V
Collector Current	I_c	1	A
Collector Dissipation	P_c	350	mW
Junction Temperature	T_j	150	
Storage Temperature	T_{STG}	-55 ~150	

SOT-23



ELECTRICAL CHARACTERISTICS ($T_A=25$)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CB0}	$I_c= 50 \mu A, I_E=0$	30			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_c= 1mA, I_B=0$	15			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E= 50 \mu A, I_c=0$	6.5			V
Collector Cut-off Current	I_{CB0}	$V_{CB}= 25V, I_E=0$			100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB}= 6V, I_c=0$			100	nA
DC Current Gain	H_{FE}	$V_{CE}= 3V, I_c= 100mA$	150			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c= 1000mA, I_B= 100mA$		0.3	0.4	V
Transition Frequency	f_T	$V_{CE}= 5V, I_c= 50mA$		260		MHz
Collector Output Capacitance	C_{ob}	$f=1MHz, V_{CB}= 10V, I_E= 0$		5		pF